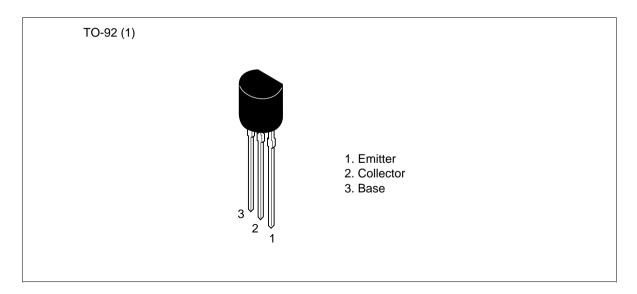
Silicon PNP Epitaxial

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Application

- Low frequency low noise amplifier
- Complementary pair with 2SC1775/A

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

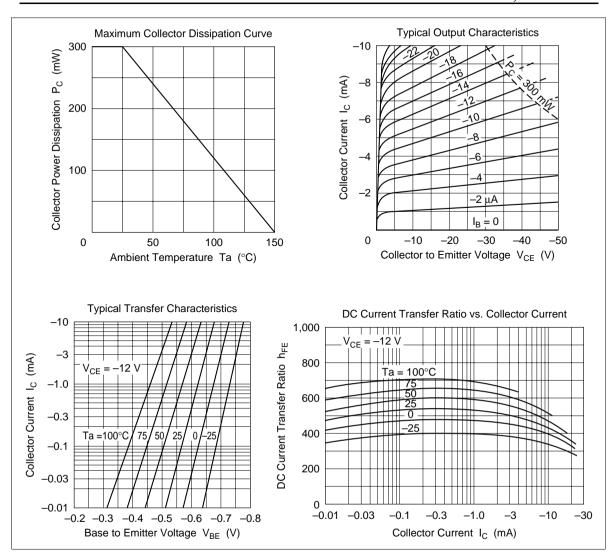
Item	Symbol	2SA872	2SA872A	Unit
Collector to base voltage	V_{CBO}	-90	-120	V
Collector to emitter voltage	V _{CEO}	-90	-120	V
Emitter to base voltage	V_{EBO}	- 5	– 5	V
Collector current	Ic	-50	– 50	mA
Collector power dissipation	P _c	300	300	mW
Junction temperature	Tj	150	150	°C
Storage temperature	Tstg	-55 to +150	-50 to +150	°C

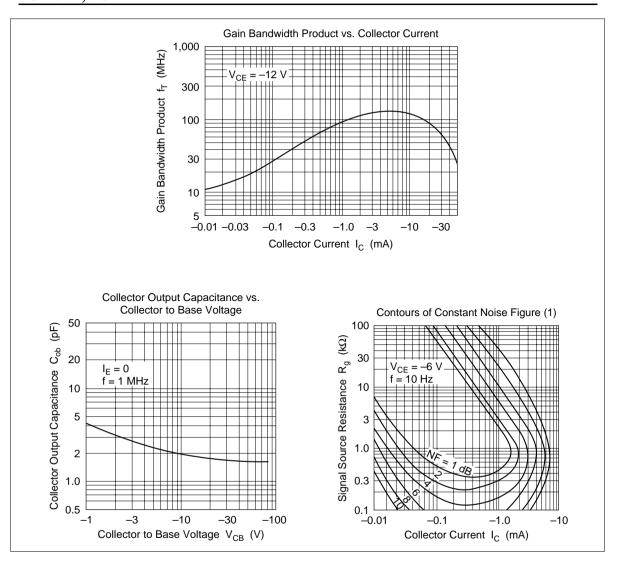
Electrical Characteristics (Ta = 25°C)

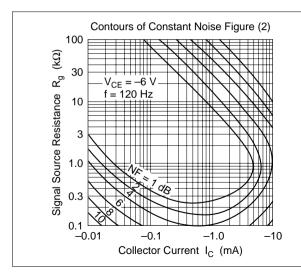
		2SA8	372		2SA872A				
Item	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-90	_	_	-120	_	_	V	$I_{\rm C} = -1 \text{ mA}, R_{\rm BE} = \infty$
Collector cutoff current	I _{CBO}	_	_	-0.5	_	_	_	μΑ	$V_{CB} = -75 \text{ V}, I_{E} = 0$
		_	_	_	_	_	-0.5	μΑ	$V_{CE} = -100 \text{ V}, I_{E} = 0$
DC current tarnsfer ratio	h _{FE1} *1	250	_	800	250	_	800		$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
	h _{FE2}	160	_	_	160	_	_		$V_{CE} = -12 \text{ V},$ $I_{C} = -0.1 \text{ mA}$
Base to emitter voltage	V_{BE}	_	_	-0.75	_	_	-0.75	V	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.5	_	_	-0.5	V	$I_{\rm C} = -10 \text{ mA},$ $I_{\rm B} = -1 \text{ mA}$
Gain bandwidth product	f _T	_	120	_	_	120	_	MHz	$V_{CE} = -12 \text{ V},$ $I_{C} = -2 \text{ mA}$
Collector output capacitance	Cob	_	1.8	_	_	1.8	_	pF	$V_{CB} = -25 \text{ V}, I_{E} = 0,$ f = 1 MHz
Noise figure	NF	_	_	5.0		_	5.0	dB	$V_{CE} = -6 \text{ V}, f = 10 \text{ Hz}$ $I_{C} = -50 \mu\text{A}$ $R_{g} = 50 k\Omega$
		_	_	1.5	_	_	1.5	dB	f = 1 kHz

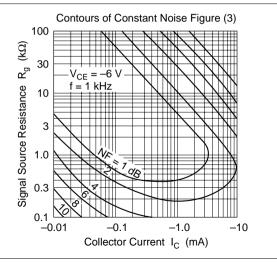
Note: 1. The 2SA872/A is grouped by h_{FE1} as follows.

D	<u>E</u>
250 to 500	400 to 800

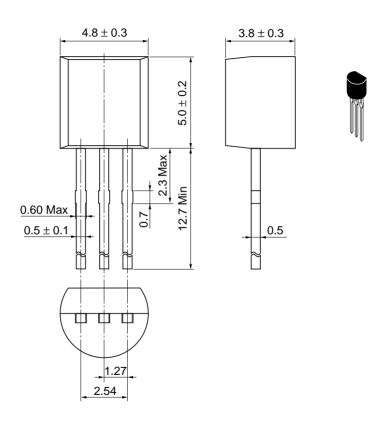








Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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